CLAIMS

1. A semiconductor structure, comprising:

several first patterns arranged in a first direction and located in a photoresist layer with a thickness greater than 1.2 um, and several second patterns arranged in a second direction, wherein the first direction and the second direction have an included angle;

wherein the first patterns have a first arrangement length in the first direction; the second patterns have a second arrangement length in the second direction; and

the first patterns are patterns with gaps, each of the first patterns has a width of 0.5 um to 1.5 um, and/or a spacing between two adjacent ones of the first patterns is 0.5 um to 1.5 um; the second patterns are photoresist patterns, each of the second patterns having a width of 1.5 um to 3.5 um and a spacing between two adjacent ones of the second patterns is 0.5 um to 1.5 um; and

an area sum of the first patterns and the second patterns is less than 1/2 of a product of the first arrangement length and the second arrangement length.

2. The semiconductor structure of claim 1, wherein the first patterns are arranged at equal intervals in a first direction, and the second patterns are arranged at equal intervals in a second direction.

3. The semiconductor structure of claim 1, wherein an included angle between the first direction and the second direction is 90 degrees.

4. The semiconductor structure of claim 1, wherein several first graphs and several second graphs are further formed in the photoresist layer; an arrangement direction of the first graphs is parallel to the first direction; and an arrangement of the second graphs is parallel to the second direction.

5. The semiconductor structure of claim 4, wherein the first graphs are graphs with gaps, and the second graphs are photoresist graphs.

6. The semiconductor structure of claim 5, wherein a width of each of the first graphs is 0.5 um to 1.5 um, and a width of each of the second graphs is 1.5 um to 3.5

um.

7. The semiconductor structure of claim 1, wherein a distance from the first patterns to the second patterns is greater than a sum of the spacing between the first patterns and the spacing between the second patterns.